

## isc N-Channel MOSFET Transistor

## PSMN3R3-80BS

## FEATURES

- Drain Current  $-I_D = 120A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DS} = 80V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 3.5m\Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## DESCRIPTION

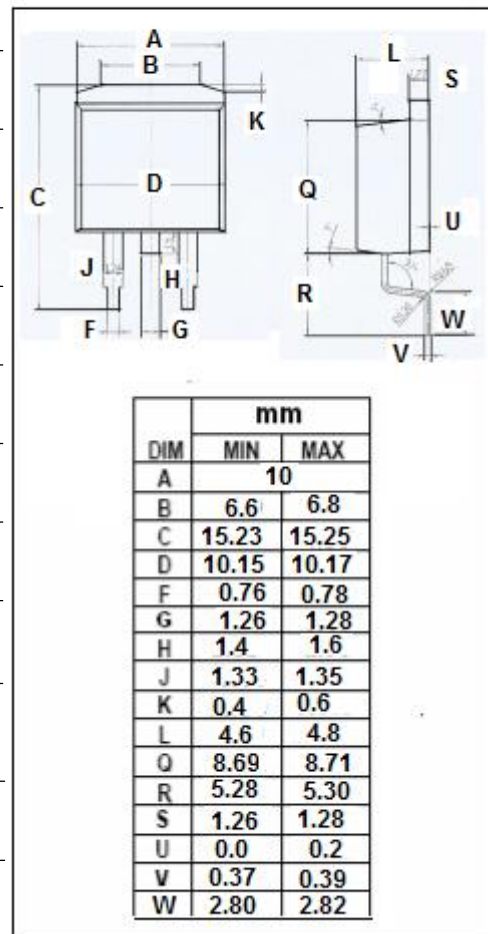
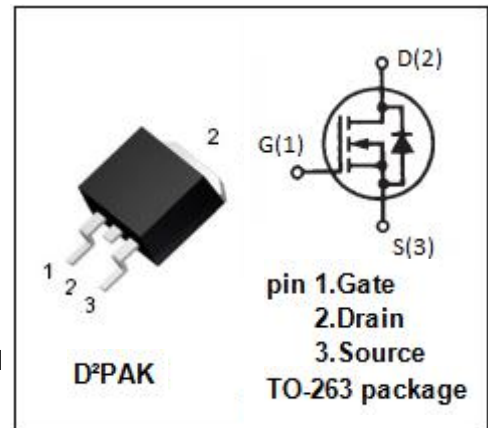
- Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )

| SYMBOL    | PARAMETER                              | VALUE    | UNIT       |
|-----------|----------------------------------------|----------|------------|
| $V_{DS}$  | Drain-Source Voltage                   | 80       | V          |
| $V_{GS}$  | Gate-Source Voltage-Continuous         | $\pm 20$ | V          |
| $I_D$     | Drain Current-Continuous               | 120      | A          |
| $I_{DM}$  | Drain Current-Single Pluse             | 760      | A          |
| $P_D$     | Total Dissipation @ $T_C = 25^\circ C$ | 306      | W          |
| $T_J$     | Max. Operating Junction Temperature    | -55~175  | $^\circ C$ |
| $T_{stg}$ | Storage Temperature                    | -55~175  | $^\circ C$ |

## THERMAL CHARACTERISTICS

| SYMBOL       | PARAMETER                            | MAX  | UNIT         |
|--------------|--------------------------------------|------|--------------|
| $R_{th j-c}$ | Thermal Resistance, Junction to Case | 0.49 | $^\circ C/W$ |



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## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                       | CONDITIONS                                               | MIN | MAX  | UNIT |
|----------------------|---------------------------------|----------------------------------------------------------|-----|------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA             | 60  |      | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 1mA | 2.0 | 4.0  | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 25A              |     | 3.5  | mΩ   |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0              |     | ±100 | nA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 80V; V <sub>GS</sub> = 0               |     | 10   | μA   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> = 25A; V <sub>GS</sub> = 0                |     | 1.2  | V    |

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